

# 64K x 4 Static RAM with Separate IO

**CY7C192** 

### Features

- High speed
  □ 15 ns
- CMOS for optimum speed/power
- Low active power 860 mW
- Low standby power □ 55 mW
- TTL-compatible inputs and outputs
- Automatic power down when deselected
- Available in Pb-free and non Pb-free 28-Pin Molded SOJ package

### **Functional Description**

The CY7C192 is a high performance CMOS static RAM organized as  $65,536 \times 4$  bits with separate IO. Easy <u>memory</u> expansion is provided by active LOW Chip Enable (CE) and tri-state drivers. It has an automatic power down feature that reduces power consumption by 75% when deselected.

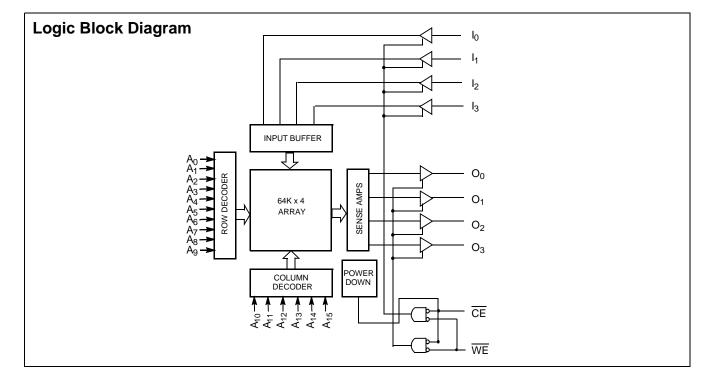
Writing to the device is accomplished when the Chip Enable  $\overline{(CE)}$  and write enable  $\overline{(WE)}$  inputs are both LOW.

Data on the four input pins ( $I_0$  through  $I_3$ ) is written into the memory location specified on the address pins ( $A_0$  through  $A_{15}$ ).

<u>Rea</u>ding the device is accomplished by taking the Chip Enable  $\overline{(CE)}$  LOW while the Write Enable (WE) remains HIGH. Under these conditions, the contents of the memory location specified on the address pins appears on the four data output pins.

 $\label{eq:thm:product} \begin{array}{l} \underline{\mathsf{The}} \text{ output pins stay in high im} \underline{\mathsf{ped}} ance state when Write Enable} \\ (WE) \text{ is LOW or Chip Enable (CE) is HIGH.} \end{array}$ 

A die coat ensures alpha immunity.



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# **Pin Configuration**

### Figure 1. 28-Pin Molded SOJ Package

Top View			
A <sub>6</sub> A <sub>7</sub> A <sub>8</sub> A <sub>9</sub> A <sub>10</sub> A <sub>11</sub> A <sub>12</sub> A <sub>13</sub> A <sub>14</sub> A <sub>15</sub> I <sub>0</sub> I <sub>1</sub> CE	1 2 3 4 5 6 7 8 9 10 11 12 13	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	
	14	16 O <sub>0</sub> 15 WE	

### **Selection Guide**

Description	-15	Unit
Maximum Access Time	15	ns
Maximum Operating Current	145	mA
Maximum CMOS Standby Current	10	mA



# **Maximum Ratings**

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested

Storage Temperature	65°C to +150°C
Ambient Temperature with Power Applied	–55°C to +125°C
Supply Voltage to Ground Potential	–0.5V to +7.0V
DC Voltage Applied to Outputs in High Z State <sup>[1]</sup>	–0.5V to $V_{CC}$ + 0.5V

DC Input Voltage <sup>[1]</sup>	. –0.5V to V <sub>CC</sub> + 0.5V
Output Current into Outputs (LOW)	20 mA
Static Discharge Voltage (per MIL-STD-883, Method 3015)	>900V
Latch-Up Current	>200 mA

# **Operating Range**

Range	Ambient Temperature <sup>[2]</sup>	V <sub>cc</sub>	
Commercial	0°C to +70°C	$5V\pm10\%$	

# **Electrical Characteristics**

Over the Operating Range

Parameter	Description	Test Canditions		-15	
	Description	Test Conditions	Min	Max	Unit
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = -4.0 mA	2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA		0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	V <sub>CC</sub> + 0.3V	V
V <sub>IL</sub>	Input LOW Voltage <sup>[1]</sup>		-0.5	0.8	V
I <sub>IX</sub>	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	-5	+5	μΑ
I <sub>OZ</sub>	Output Leakage Current	$GND \leq V_O \leq V_{CC}$ , Output Disabled	-5	+5	μΑ
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	$V_{CC} = Max. I_{OUT} = 0 mA,$ f = f <sub>MAX</sub> = 1/t <sub>RC</sub>		145	mA
I <sub>SB1</sub>	Automatic CE Power Down Current—TTL Inputs	$\begin{array}{c} \text{Max. } V_{CC}, \overline{CE} \geq V_{IH}, V_{IN} \geq V_{IH} \text{ or} \\ V_{IN} \leq V_{IL}, f = f_{MAX} \end{array}$		30	mA
I <sub>SB2</sub>	Automatic CE Power Down Current—CMOS Inputs	$\begin{array}{l} \text{Max. } V_{CC}, \ \overline{\text{CE}} \geq V_{CC} - 0.3\text{V}, \\ V_{\text{IN}} \geq V_{CC} - 0.3\text{V or } V_{\text{IN}} \leq 0.3\text{V}, \text{f} = 0 \end{array}$		10	mA

### Capacitance

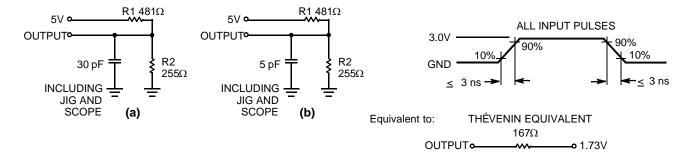
Parameter	Description	Test Conditions	Max	Unit
C <sub>IN</sub> <sup>[3]</sup>	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	8	pF
C <sub>OUT</sub> <sup>[3]</sup>	Output Capacitance	$V_{CC} = 5.0V$	10	pF

Notes

Minimum voltage is equal to -2.0V for pulse durations of less than 20 ns.
 T<sub>A</sub> is the case temperature.
 Tested initially and after any design or process changes that may affect these parameters.



#### Figure 2. AC Test Loads and Waveforms



### **Switching Characteristics**

Over the Operating Range<sup>[4]</sup>

		-	-15		
Parameter	Description	Min	Max	Unit	
Read Cycle	·	·			
t <sub>RC</sub>	Read Cycle Time	15		ns	
t <sub>AA</sub>	Address to Data Valid		15	ns	
t <sub>OHA</sub>	Output Hold from Address Change	3		ns	
t <sub>ACE</sub>	CE LOW to Data Valid		15	ns	
t <sub>LZCE</sub>	CE LOW to Low Z <sup>[5]</sup>	3		ns	
t <sub>HZCE</sub>	CE HIGH to High Z <sup>[5,6]</sup>		7	ns	
t <sub>PU</sub>	CE LOW to Power Up	0		ns	
t <sub>PD</sub>	CE HIGH to Power Down		15	ns	
Write Cycle <sup>[7]</sup>	·	ŀ			
t <sub>WC</sub>	Write Cycle Time	15		ns	
t <sub>SCE</sub>	CE LOW to Write End	10		ns	
t <sub>AW</sub>	Address Setup to Write End	10		ns	
t <sub>HA</sub>	Address Hold from Write End	0		ns	
t <sub>SA</sub>	Address Setup to Write Start	0		ns	
t <sub>PWE</sub>	WE Pulse Width	9		ns	
t <sub>SD</sub>	Data Setup to Write End			ns	
t <sub>HD</sub>	Data Hold from Write End 0		ns		
t <sub>LZWE</sub>	WE HIGH to Low Z <sup>[5]</sup>	3 ns		ns	
t <sub>HZWE</sub>	WE LOW to High Z <sup>[5, 6]</sup>	7 ns		ns	

#### Notes

Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub> and 30-pF load capacitance.

At any temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZWE</sub> is less than t<sub>LZCE</sub> for any given device. These parameters are guaranteed by design and 5. not 100% tested.

6.

 $t_{HZCE}$  and  $t_{HZWE}$  are specified with  $C_L = 5 \text{ pF}$  as in part (b) of AC Test Loads. Transition is measured  $\pm 500 \text{ mV}$  from steady-state voltage. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input setup and hold timing must be referenced to the rising edge of the signal that terminates the write. 7.

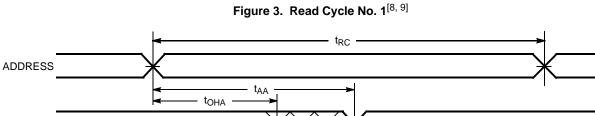


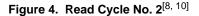
DATA VALID

### **Switching Waveforms**

PREVIOUS DATA VALID

DATA OUT





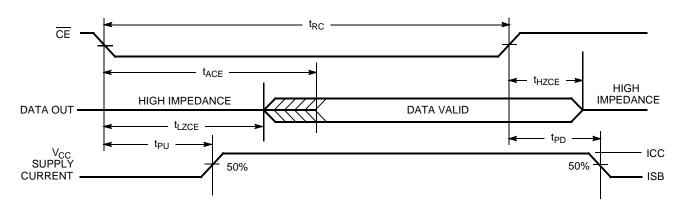
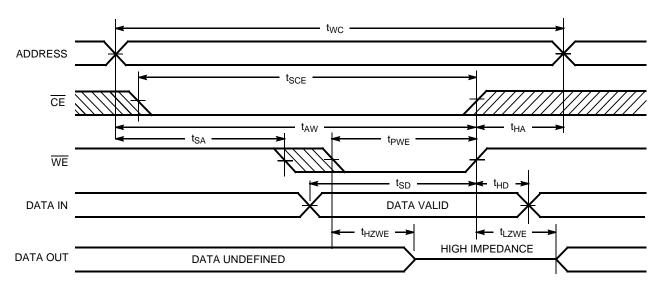


Figure 5. Write Cycle No. 1 (WE Controlled)<sup>[7]</sup>



Notes8.WE is HIGH for read cycle.9.Device is continuously selected,  $\overline{CE} = V_{IL}$ .10.Address valid prior to or coincident with CE transition LOW.



# Switching Waveforms (continued)

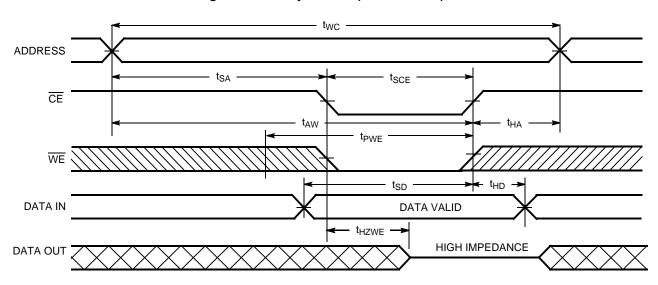
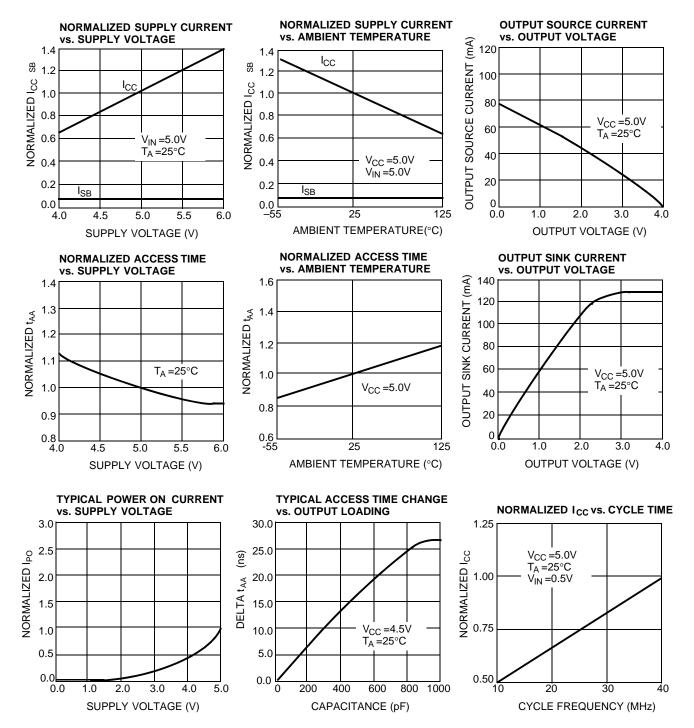


Figure 6. Write Cycle No. 2 (CE Controlled)<sup>[7, 11]</sup>





### **Typical DC and AC Characteristics**





### **Ordering Information**

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY7C192-15VC	51-85031	28-Pin Molded SOJ	Commercial
	CY7C192-15VXC		28-Pin Molded SOJ (Pb-free)	

### Package Diagram



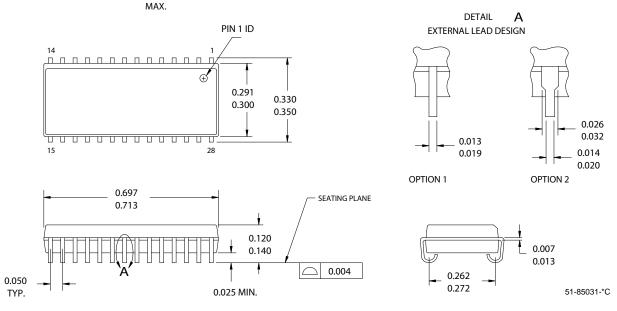
NOTE :

1. JEDEC STD REF MO088

2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH

MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE MIN.

3. DIMENSIONS IN INCHES





### **Document History Page**

	Document Title: CY7C192 64K x 4 Static RAM with Separate IO Document Number: 38-05047				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change	
**	107149	09/10/01	SZV	Change Spec number from: 38-00076 to 38-05047	
*A	359716	See ECN	AJU	Changed Static Discharge Voltage limit in the Maximum Ratings section (page 2) from 2001V to 900V Removed references to CY7C191	
*В	419549	See ECN	AJU	Added Pb-free parts to the Ordering Information table and replaced the Package Name column with Package Diagram	
*C	492500	See ECN	NXR	Removed 20 ns and 25 ns speed bins Changed the Low active power from 220 mW to 55 mW Changed the description of $I_{IX}$ from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Removed $I_{OS}$ parameter from DC Electrical Characteristics table Removed 28-Lead (300-Mil) PDIP package from product offering Updated Ordering Information table	
*D	2104606	See ECN	VKN/AESA	Removed 12 ns speed bin	

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